

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $\pi$ -MOSIV)

# 2SK3566

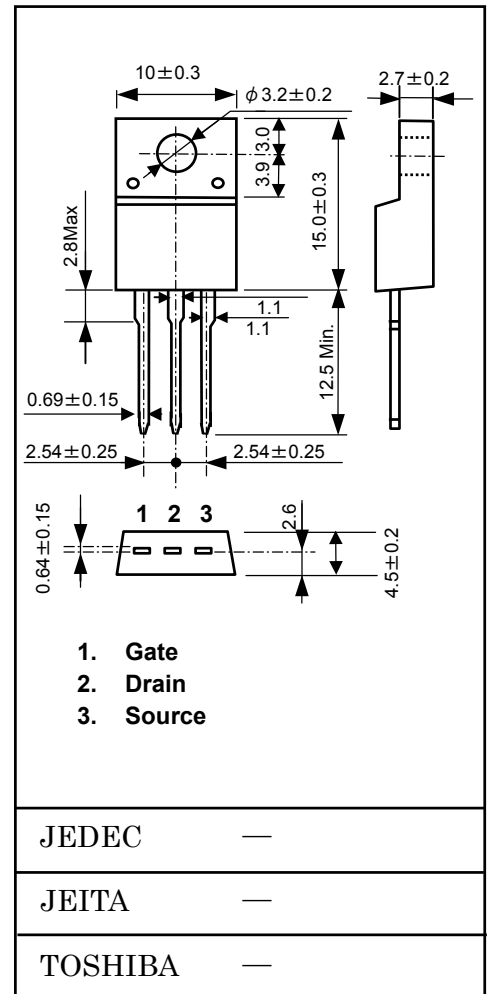
unit : mm

## Switching Regulator Applications

- Low drain-source ON resistance:  $R_{DS(ON)} = 5.6 \Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 2.0 S$  (typ.)
- Low leakage current:  $I_{DSS} = 100 \mu A$  ( $V_{DS} = 720 V$ )
- Enhancement-mode:  $V_{th} = 2.0 \sim 4.0 V$  ( $V_{DS} = 10 V, I_D = 1 mA$ )

## Maximum Ratings ( $T_a = 25^\circ C$ )

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	900	V
Drain-gate voltage ( $R_{GS} = 20 k\Omega$ )		$V_{DGR}$	900	V
Gate-source voltage		$V_{GSS}$	$\pm 30$	V
Drain current	DC (Note 1)	$I_D$	2.5	A
	Pulse ( $t = 1 ms$ ) (Note 1)	$I_{DP}$	7.5	
Drain power dissipation ( $T_c = 25^\circ C$ )		$P_D$	40	W
Single pulse avalanche energy (Note 2)		$E_{AS}$	216	mJ
Avalanche current		$I_{AR}$	2.5	A
Repetitive avalanche energy (Note 3)		$E_{AR}$	4	mJ
Channel temperature		$T_{ch}$	150	$^\circ C$
Storage temperature range		$T_{stg}$	-55~150	$^\circ C$



## Thermal Characteristics

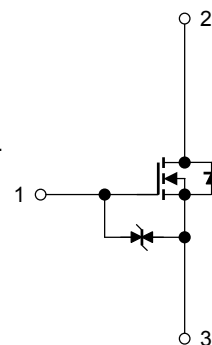
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	3.125	$^\circ C/W$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	62.5	$^\circ C/W$

Note 1: Please use devices on conditions that the channel temperature is below  $150^\circ C$ .

Note 2:  $V_{DD} = 90 V, T_{ch} = 25^\circ C, L = 63.4 mH, I_{AR} = 2.5 A, R_G = 25 \Omega$

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.



## Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Gate-source breakdown voltage		$V_{(BR)GSS}$	$I_D = \pm 10\ \mu\text{A}, V_{GS} = 0\text{ V}$	$\pm 30$	—	—	V
Drain cut-off current		$I_{DSS}$	$V_{DS} = 720\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	900	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	2.0	—	4.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 1.5\text{ A}$	—	5.6	6.4	$\Omega$
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 20\text{ V}, I_D = 1.5\text{ A}$	1.0	2.0	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	470	—	pF
Reverse transfer capacitance		$C_{rss}$		—	10	—	
Output capacitance		$C_{oss}$		—	50	—	
Switching time	Rise time	$t_r$	<p><math>I_D = 1.5\text{ A}</math> <math>V_{GS} = 10\text{ V}</math> <math>V_{DD} \approx 200\text{ V}</math> <math>R_L = 133\ \Omega</math> Duty <math>\leq 1\%</math>, <math>t_w = 10\ \mu\text{s}</math></p>	—	20	—	ns
	Turn-on time	$t_{on}$		—	60	—	
	Fall time	$t_f$		—	30	—	
	Turn-off time	$t_{off}$		—	100	—	
Total gate charge		$Q_g$	$V_{DD} \approx 400\text{ V}, V_{GS} = 10\text{ V}, I_D = 2.5\text{ A}$	—	12	—	nC
Gate-source charge		$Q_{gs}$		—	7	—	
Gate-drain charge		$Q_{gd}$		—	5	—	

## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)		$I_{DR}$	—	—	—	2.5	A
Pulse drain reverse current (Note 1)		$I_{DRP}$	—	—	—	7.5	A
Forward voltage (diode)		$V_{DSF}$	$I_{DR} = 2.5\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.7	V
Reverse recovery time		$t_{rr}$	$I_{DR} = 2.5\text{ A}, V_{GS} = 0\text{ V},$	—	720	—	ns
Reverse recovery charge		$Q_{rr}$	$dI_{DR}/dt = 100\text{ A}/\mu\text{s}$	—	3.6	—	$\mu\text{C}$

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